

Title (en)  
SEMICONDUCTOR COMPONENT AND METHOD FOR PRODUCING A SEMICONDUCTOR COMPONENT IN A SUBSTRATE HAVING A CRYSTALLOGRAPHIC (100) ORIENTATION

Title (de)  
HALBLEITERBAUELEMENT SOWIE EIN VERFAHREN ZUR ERZEUGUNG EINES HALBLEITERBAUELEMENTES IN EINEM EINE KRISTALLOGRAPHISCHE (100)-ORIENTIERUNG AUFWEISENDEN SUBSTRAT

Title (fr)  
COMPOSANT À SEMI-CONDUCTEUR ET PROCÉDÉ DE FABRICATION D'UN COMPOSANT À SEMI-CONDUCTEUR DANS UN SUBSTRAT AYANT UNE ORIENTATION CRISTALLOGRAPHIQUE

Publication  
**EP 3063781 A1 20160907 (DE)**

Application  
**EP 14780877 A 20141006**

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Abstract (en)  
[origin: WO2015062817A1] The invention relates to a semiconductor component (100), comprising a substrate (90) and a gallium nitride-containing first functional element (80) which is implemented in the surface (91) of the substrate (90). The substrate (90) has a crystallographic (100) orientation. The invention further relates to a method for producing a semiconductor element (100) in a substrate (90) having a crystallographic (100) orientation.

IPC 8 full level  
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Citation (search report)  
See references of WO 2015062817A1

Citation (examination)  
• US 2011049681 A1 20110303 - VIELEMEYER MARTIN HENNING ALBRECHT [AT]  
• US 2007205407 A1 20070906 - MATSUO HISAYOSHI [JP], et al

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